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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M0
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	CANbus, HDMI-CEC, I ² C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	DMA, I ² S, POR, PWM, WDT
Number of I/O	51
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16К х 8
Voltage - Supply (Vcc/Vdd)	1.65V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f072r8t6

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

USART modes/features ⁽¹⁾	USART1 and USART2	USART3 and USART4
IrDA SIR ENDEC block	Х	-
LIN mode	Х	-
Dual clock domain and wakeup from Stop mode	X	-
Receiver timeout interrupt	X	-
Modbus communication	Х	-
Auto baud rate detection	Х	-
Driver Enable	X	Х

Table 10. STM32F072x8/xB USART ir	mplementation (continued)

1. X = supported.

3.18 Serial peripheral interface (SPI) / Inter-integrated sound interface (I²S)

Two SPIs are able to communicate up to 18 Mbit/s in slave and master modes in full-duplex and half-duplex communication modes. The 3-bit prescaler gives 8 master mode frequencies and the frame size is configurable from 4 bits to 16 bits.

Two standard I²S interfaces (multiplexed with SPI1 and SPI2 respectively) supporting four different audio standards can operate as master or slave at half-duplex communication mode. They can be configured to transfer 16 and 24 or 32 bits with 16-bit or 32-bit data resolution and synchronized by a specific signal. Audio sampling frequency from 8 kHz up to 192 kHz can be set by an 8-bit programmable linear prescaler. When operating in master mode, they can output a clock for an external audio component at 256 times the sampling frequency.

Table 11. STM32F0	72x8/xB SPI/I ² S	implementation
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SPI features ⁽¹⁾	SPI1 and SPI2
Hardware CRC calculation	Х
Rx/Tx FIFO	Х
NSS pulse mode	Х
I ² S mode	Х
TI mode	Х

1. X = supported.

3.19 High-definition multimedia interface (HDMI) - consumer electronics control (CEC)

The device embeds a HDMI-CEC controller that provides hardware support for the Consumer Electronics Control (CEC) protocol (Supplement 1 to the HDMI standard).

This protocol provides high-level control functions between all audiovisual products in an environment. It is specified to operate at low speeds with minimum processing and memory



overhead. It has a clock domain independent from the CPU clock, allowing the HDMI_CEC controller to wakeup the MCU from Stop mode on data reception.

3.20 Controller area network (CAN)

The CAN is compliant with specifications 2.0A and B (active) with a bit rate up to 1 Mbit/s. It can receive and transmit standard frames with 11-bit identifiers as well as extended frames with 29-bit identifiers. It has three transmit mailboxes, two receive FIFOs with 3 stages and 14 scalable filter banks.

3.21 Universal serial bus (USB)

The STM32F072x8/xB embeds a full-speed USB device peripheral compliant with the USB specification version 2.0. The internal USB PHY supports USB FS signaling, embedded DP pull-up and also battery charging detection according to Battery Charging Specification Revision 1.2. The USB interface implements a full-speed (12 Mbit/s) function interface with added support for USB 2.0 Link Power Management. It has software-configurable endpoint setting with packet memory up-to 1 KB (the last 256 byte are used for CAN peripheral if enabled) and suspend/resume support. It requires a precise 48 MHz clock which can be generated from the internal main PLL (the clock source must use an HSE crystal oscillator) or by the internal 48 MHz oscillator in automatic trimming mode. The synchronization for this oscillator can be taken from the USB data stream itself (SOF signalization) which allows crystal-less operation.

3.22 Clock recovery system (CRS)

The STM32F072x8/xB embeds a special block which allows automatic trimming of the internal 48 MHz oscillator to guarantee its optimal accuracy over the whole device operational range. This automatic trimming is based on the external synchronization signal, which could be either derived from USB SOF signalization, from LSE oscillator, from an external signal on CRS_SYNC pin or generated by user software. For faster lock-in during startup it is also possible to combine automatic trimming with manual trimming action.

3.23 Serial wire debug port (SW-DP)

An ARM SW-DP interface is provided to allow a serial wire debugging tool to be connected to the MCU.



4 Pinouts and pin descriptions



Figure 3. UFBGA100 package pinout



5 Memory mapping

To the difference of STM32F072xB memory map in *Figure 10*, the two bottom code memory spaces of STM32F072x8 end at 0x0000 FFFF and 0x0800 FFFF, respectively.



Figure 10. STM32F072xB memory map



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6.2 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in *Table 21: Voltage characteristics*, *Table 22: Current characteristics* and *Table 23: Thermal characteristics* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

Symbol	Ratings	Min	Max	Unit
V _{DD} -V _{SS}	External main supply voltage	- 0.3	4.0	V
V _{DDIO2} -V _{SS}	External I/O supply voltage	- 0.3	4.0	V
$V_{DDA} - V_{SS}$	External analog supply voltage	- 0.3	4.0	V
V _{DD} -V _{DDA}	Allowed voltage difference for $V_{DD} > V_{DDA}$	-	0.4	V
V _{BAT} –V _{SS}	External backup supply voltage	- 0.3	4.0	V
V ⁽²⁾	Input voltage on FT and FTf pins	V _{SS} - 0.3	V _{DDIOx} + 4.0 ⁽³⁾	V
	Input voltage on TTa pins	V _{SS} - 0.3	4.0	V
VIN` '	BOOT0	0	9.0	V
	Input voltage on any other pin	V _{SS} - 0.3	4.0	V
ΔV _{DDx}	Variations between different V_{DD} power pins	-	50	mV
V _{SSx} - V _{SS}	Variations between all the different ground pins	-	50	mV
V _{ESD(HBM)}	Electrostatic discharge voltage (human body model)	see Section 6.3 sensitivity chara	.12: Electrical acteristics	-

1. All main power (V_{DD} , V_{DDA}) and ground (V_{SS} , V_{SSA}) pins must always be connected to the external power supply, in the permitted range.

2. V_{IN} maximum must always be respected. Refer to *Table 22: Current characteristics* for the maximum allowed injected current values.

3. Valid only if the internal pull-up/pull-down resistors are disabled. If internal pull-up or pull-down resistor is enabled, the maximum limit is 4 V.



Symbol	Ratings	Max.	Unit
ΣI _{VDD}	Total current into sum of all VDD power lines (source) ⁽¹⁾	120	
ΣI _{VSS}	Total current out of sum of all VSS ground lines (sink) ⁽¹⁾	-120	
I _{VDD(PIN)}	Maximum current into each VDD power pin (source) ⁽¹⁾	100	
I _{VSS(PIN)}	Maximum current out of each VSS ground pin (sink) ⁽¹⁾	-100	
	Output current sunk by any I/O and control pin	25	
IIO(PIN)	Output current source by any I/O and control pin	-25	
	Total output current sunk by sum of all I/Os and control pins ⁽²⁾	80	
ΣΙ _{ΙΟ(ΡΙΝ)}	Total output current sourced by sum of all I/Os and control pins ⁽²⁾	-80	mA
	Total output current sourced by sum of all I/Os supplied by VDDIO2	-40	
	Injected current on B, FT and FTf pins	-5/+0 ⁽⁴⁾	
I _{INJ(PIN)} ⁽³⁾	Injected current on TC and RST pin	± 5	
	Injected current on TTa pins ⁽⁵⁾	± 5	
ΣI _{INJ(PIN)}	Total injected current (sum of all I/O and control pins) ⁽⁶⁾	± 25	1

Table 22. Current characteristics

1. All main power (VDD, VDDA) and ground (VSS, VSSA) pins must always be connected to the external power supply, in the permitted range.

2. This current consumption must be correctly distributed over all I/Os and control pins. The total output current must not be sunk/sourced between two consecutive power supply pins referring to high pin count QFP packages.

A positive injection is induced by V_{IN} > V_{DDIOx} while a negative injection is induced by V_{IN} < V_{SS}. I_{INJ(PIN)} must never be exceeded. Refer to *Table 21: Voltage characteristics* for the maximum allowed input voltage values.

4. Positive injection is not possible on these I/Os and does not occur for input voltages lower than the specified maximum value.

5. On these I/Os, a positive injection is induced by $V_{IN} > V_{DDA}$. Negative injection disturbs the analog performance of the device. See note ⁽²⁾ below *Table 59: ADC accuracy*.

6. When several inputs are submitted to a current injection, the maximum $\Sigma I_{INJ(PIN)}$ is the absolute sum of the positive and negative injected currents (instantaneous values).

Table 23. Thermal characteristics

Symbol	Ratings	Value	Unit
T _{STG}	Storage temperature range	–65 to +150	°C
TJ	Maximum junction temperature	150	°C



6.3 Operating conditions

6.3.1 General operating conditions

Symbol	Parameter	Conditions	Min	Мах	Unit			
f _{HCLK}	Internal AHB clock frequency	-	0	48	Mu-			
f _{PCLK}	Internal APB clock frequency	-	0	48				
V _{DD}	Standard operating voltage	-	2.0	3.6	V			
V _{DDIO2}	I/O supply voltage	Must not be supplied if V_{DD} is not present	1.65	3.6	V			
V _{DDA} V _{BAT}	Analog operating voltage (ADC and DAC not used)	Must have a potential equal	V_{DD}	3.6				
	Analog operating voltage (ADC and DAC used)	to or higher than V _{DD}	2.4	3.6	v			
V _{BAT}	Backup operating voltage	-	1.65	3.6	V			
V _{IN}		TC and RST I/O	-0.3	V _{DDIOx} +0.3				
		TTa I/O	-0.3	V _{DDA} +0.3 ⁽¹⁾	V			
		FT and FTf I/O	-0.3	5.5 ⁽¹⁾				
		BOOT0	0	5.5				
		-	364					
		LQFP100	-	476				
	Power dissipation at $T_{A} = 85 \ ^{\circ}C$	UFBGA64	-	308				
PD	for suffix 6 or $T_A = 105 \degree C$ for	LQFP64	455	mW				
	suffix 7 ⁽²⁾	LQFP48	-	370				
		UFQFPN48	-	625				
		WLCSP49	-	408				
	Ambient temperature for the	Maximum power dissipation	-40	85	°C			
т	suffix 6 version	Low power dissipation ⁽³⁾	-40	105	C			
Та	Ambient temperature for the	Maximum power dissipation	-40	105	°C			
	suffix 7 version	Low power dissipation ⁽³⁾	-40	125				
T.		Suffix 6 version	-40	105	°C			
IJ		Suffix 7 version	-40	125	C			

Table 24. General operating conditions

1. For operation with a voltage higher than V_{DDIOx} + 0.3 V, the internal pull-up resistor must be disabled.

2. If T_A is lower, higher P_D values are allowed as long as T_J does not exceed T_{Jmax} . See Section 7.8: Thermal characteristics.

 In low power dissipation state, T_A can be extended to this range as long as T_J does not exceed T_{Jmax} (see Section 7.8: Thermal characteristics).



	er			All	peripher	als enab	led ⁽¹⁾	All	periphe	rals disa	abled		
Iodm	amete	Conditions	f _{HCLK}		M	lax @ T _A	(2)		Max @ T _A ⁽²⁾			Unit	
Sy	Para			Тур	25 °C	85 °C	105 °C	Тур	25 °C	85 °C	105 °C		
		HSI48	48 MHz	23.1	25.4	25.8	26.6	12.8	13.5	13.7	13.9		
			48 MHz	23.0	25.3 ⁽³⁾	25.7	26.5 ⁽³⁾	12.6	13.3 ⁽³⁾	13.5	13.8 ⁽³⁾		
	ode, AM	HSE bypass, PLL on	32 MHz	15.4	17.3	17.8	18.3	7.96	8.92	9.17	9.73		
	u n N N N		24 MHz	11.4	12.9	13.5	13.7	6.48	8.04	8.23	8.41		
	n Ru g fro	HSE bypass,	8 MHz	4.21	4.6	4.89	5.25	2.07	2.3	2.35	2.94		
	ent i utinę	PLL off	1 MHz	0.78	0.9	0.92	1.15	0.36	0.48	0.59	0.82		
	curre		48 MHz	23.1	24.5	25.0	25.2	12.6	13.7	13.9	14.0		
	pply ode	HSI clock, PLL on	32 MHz	15.4	17.4	17.7	18.2	8.05	8.85	9.16	9.94		
	Sul		24 MHz	11.5	13.0	13.6	13.9	6.49	8.06	8.21	8.47		
		HSI clock, PLL off	8 MHz	4.34	4.75	5.03	5.41	2.11	2.36	2.38	2.98	m 4	
'DD		HSI48	48 MHz	15.1	16.6	16.8	17.5	3.08	3.43	3.56	3.61	ШA	
	0		48 MHz	15.0	16.5 ⁽³⁾	16.7	17.3 ⁽³⁾	2.93	3.28 ⁽³⁾	3.41	3.46 ⁽³⁾		
	pode	HSE bypass, PLL on	32 MHz	9.9	11.4	11.6	11.9	2.0	2.24	2.32	2.49		
	ep r		24 MHz	7.43	8.17	8.71	8.82	1.63	1.82	1.88	1.9		
	n Sle	n Sle	HSE bypass,	8 MHz	2.83	3.09	3.26	3.66	0.76	0.88	0.91	0.93	
	ent ir	PLL off	1 MHz	0.42	0.54	0.55	0.67	0.28	0.39	0.41	0.43		
	curre		48 MHz	15.0	17.2	17.3	17.9	3.04	3.37	3.41	3.46		
	ply	HSI clock, PLL on	32 MHz	9.93	11.3	11.6	11.7	2.11	2.35	2.44	2.65		
	Sup		24 MHz	7.53	8.45	8.87	8.95	1.64	1.83	1.9	1.93		
		HSI clock, PLL off	8 MHz	2.95	3.24	3.41	3.8	0.8	0.92	0.94	0.97		

Table	29. T	ypical a	nd max	kimum (current	consun	nption	from	V_{DD}	supply	at V _I	_{DD} = 3	.6 V	(contin	ued)

1. USB is kept disabled as this IP functions only with a 48 MHz clock.

2. Data based on characterization results, not tested in production unless otherwise specified.

3. Data based on characterization results and tested in production (using one common test limit for sum of I_{DD} and I_{DDA}).



On-chip peripheral current consumption

The current consumption of the on-chip peripherals is given in *Table 35*. The MCU is placed under the following conditions:

- All I/O pins are in analog mode
- All peripherals are disabled unless otherwise mentioned
- The given value is calculated by measuring the current consumption
 - with all peripherals clocked off
 - with only one peripheral clocked on
- Ambient operating temperature and supply voltage conditions summarized in *Table 21: Voltage characteristics*
- The power consumption of the digital part of the on-chip peripherals is given in *Table 35.* The power consumption of the analog part of the peripherals (where applicable) is indicated in each related section of the datasheet.

	Peripheral	Typical consumption at 25 °C	Unit
	BusMatrix ⁽¹⁾	2.2	
	CRC	1.6	
	DMA	5.7	
	Flash memory interface	13.0	
	GPIOA	8.2	
AHB	GPIOB	8.5	
	GPIOC	2.3	µA/MHz
	GPIOD	1.9	
	GPIOE	2.2	
	GPIOF	1.2	
	SRAM	0.9	
	TSC	5.0	
	All AHB peripherals	52.6	

Table 35. Peripheral current consumption



	Peripheral	Typical consumption at 25 °C	Unit
	APB-Bridge ⁽²⁾	2.8	
	ADC ⁽³⁾	4.1	
	CAN	12.4	
	CEC	1.5	
	CRS	0.8	
	DAC ⁽³⁾	4.7	
	DEBUG (MCU debug feature)	0.1	
	I2C1	3.9	
	I2C2	4.0	
	PWR	1.3	
АРВ	SPI1	8.7	
	SPI2	8.5	
	SYSCFG & COMP	1.7	
	TIM1	14.9	
	TIM2	15.5	
	TIM3	11.4	µA/MHz
	TIM6	2.5	
	TIM7	2.3	
	TIM14	5.3	
	TIM15	9.1	
	TIM16	6.6	
	TIM17	6.8	
	USART1	17.0	
	USART2	16.7	
	USART3	5.4	
	USART4	5.4	
	USB	7.2	
	WWDG	1.4	
	All APB peripherals	182	

Table 35. Peripheral current consumption (continued)

1. The BusMatrix is automatically active when at least one master is ON (CPU, DMA).

2. The APB Bridge is automatically active when at least one peripheral is ON on the Bus.

 The power consumption of the analog part (I_{DDA}) of peripherals such as ADC, DAC, Comparators, is not included. Refer to the tables of characteristics in the subsequent sections.



Low-speed internal (LSI) RC oscillator

Table 44. LSI	oscillator	characteristics ⁽¹⁾
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Symbol	Parameter	Min	Тур	Max	Unit
f _{LSI}	Frequency	30	40	50	kHz
t _{su(LSI)} ⁽²⁾	LSI oscillator startup time	-	-	85	μs
I _{DDA(LSI)} ⁽²⁾	LSI oscillator power consumption	-	0.75	1.2	μÂ

1. V_{DDA} = 3.3 V, T_A = –40 to 105 $^\circ\text{C}$ unless otherwise specified.

2. Guaranteed by design, not tested in production.

6.3.9 PLL characteristics

The parameters given in *Table 45* are derived from tests performed under ambient temperature and supply voltage conditions summarized in *Table 24: General operating conditions*.

Symbol	Parameter		Value	Unit	
Symbol	Faiameter	Min	Тур	Max	Unit
f	PLL input clock ⁽¹⁾	1 ⁽²⁾	8.0	24 ⁽²⁾	MHz
^I PLL_IN	PLL input clock duty cycle	40 ⁽²⁾	-	60 ⁽²⁾	%
f _{PLL_OUT}	PLL multiplier output clock	16 ⁽²⁾	-	48	MHz
t _{LOCK}	PLL lock time	-	-	200 ⁽²⁾	μs
Jitter _{PLL}	Cycle-to-cycle jitter	_	_	300 ⁽²⁾	ps

Table 45. PLL characteristics

1. Take care to use the appropriate multiplier factors to obtain PLL input clock values compatible with the range defined by f_{PLL_OUT}.

2. Guaranteed by design, not tested in production.

6.3.10 Memory characteristics

Flash memory

The characteristics are given at T_A = -40 to 105 °C unless otherwise specified.

Table 46. Flash memory characteristics

Symbol	Parameter	Conditions	Min	Тур	Max ⁽¹⁾	Unit
t _{prog}	16-bit programming time	T _A = - 40 to +105 °C	40	53.5	60	μs
t _{ERASE}	Page (2 KB) erase time	T _A = - 40 to +105 °C	20	-	40	ms
t _{ME}	Mass erase time	T _A = - 40 to +105 °C	20	-	40	ms
	Supply ourrept	Write mode	-	-	10	mA
I _{DD}		Erase mode	-	-	12	mA

1. Guaranteed by design, not tested in production.



Symbol	Parameter	Conditions	Min ⁽¹⁾	Unit		
N _{END}	Endurance	T _A = -40 to +105 °C	10	kcycle		
t _{RET}	Data retention	1 kcycle ⁽²⁾ at T _A = 85 °C	30			
		1 kcycle ⁽²⁾ at T _A = 105 °C	10	Year		
		10 kcycle ⁽²⁾ at T _A = 55 °C	20			

 Table 47. Flash memory endurance and data retention

1. Data based on characterization results, not tested in production.

2. Cycling performed over the whole temperature range.

6.3.11 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports). the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- Electrostatic discharge (ESD) (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- **FTB**: A Burst of Fast Transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

A device reset allows normal operations to be resumed.

The test results are given in *Table 48*. They are based on the EMS levels and classes defined in application note AN1709.

Table 48. E	MS charac	teristics
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Symbol	Parameter	Conditions	Level/ Class
V _{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	V_{DD} = 3.3 V, LQFP100, T _A = +25 °C, f _{HCLK} = 48 MHz, conforming to IEC 61000-4-2	2B
V _{EFTB}	Fast transient voltage burst limits to be applied through 100 pF on V_{DD} and V_{SS} pins to induce a functional disturbance	V_{DD} = 3.3 V, LQFP100, T _A = +25°C, f _{HCLK} = 48 MHz, conforming to IEC 61000-4-4	4B

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.





Figure 22. TC and TTa I/O input characteristics

Figure 23. Five volt tolerant (FT and FTf) I/O input characteristics



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Equation 1: R_{AIN} max formula

$$R_{AIN} < \frac{T_{S}}{f_{ADC} \times C_{ADC} \times \ln(2^{N+2})} - R_{ADC}$$

The formula above (*Equation 1*) is used to determine the maximum external impedance allowed for an error below 1/4 of LSB. Here N = 12 (from 12-bit resolution).

Table 58. R _{AIN} max for f _{ADC} = 14 MHz					
T _s (cycles)	t _S (μs)	R _{AIN} max (kΩ) ⁽¹⁾			
1.5	0.11	0.4			
7.5	0.54	5.9			
13.5	0.96	11.4			
28.5	2.04	25.2			
41.5	2.96	37.2			
55.5	3.96	50			
71.5	5.11	NA			
239.5	17.1	NA			

1. Guaranteed by design, not tested in production.

Table 59. ADC accuracy⁽¹⁾⁽²⁾⁽³⁾

Symbol	Parameter	Test conditions	Тур	Max ⁽⁴⁾	Unit
ET	Total unadjusted error		±1.3	±2	
EO	Offset error	f _{PCLK} = 48 MHz,	±1	±1.5	
EG	Gain error	$T_{ADC} = 14 \text{ MHz}, R_{AIN} < 10 \text{ k}\Omega$	±0.5	±1.5	LSB
ED	Differential linearity error	$T_A = 25 \text{ °C}$	±0.7	±1	
EL	Integral linearity error		±0.8	±1.5	
ET	Total unadjusted error		±3.3	±4	
EO	Offset error	f _{PCLK} = 48 MHz,	±1.9	±2.8	
EG	Gain error	$f_{ADC} = 14 \text{ MHZ}, R_{AIN} < 10 \text{ k}\Omega$	±2.8	±3	LSB
ED	Differential linearity error	$T_A = -40$ to 105 °C	±0.7	±1.3	
EL	Integral linearity error		±1.2	±1.7	
ET	Total unadjusted error		±3.3	±4	
EO	Offset error	f _{PCLK} = 48 MHz,	±1.9	±2.8	
EG	Gain error	$T_{ADC} = 14 \text{ MHz}, R_{AIN} < 10 \text{ k}\Omega$	±2.8	±3	LSB
ED	Differential linearity error	$T_A = 25 \text{°C}$	±0.7	±1.3	
EL	Integral linearity error		±1.2	±1.7	

1. ADC DC accuracy values are measured after internal calibration.



Symbol	Parameter	Conditio	ons	Min ⁽¹⁾	Тур	Max ⁽¹⁾	Unit
V _{hys}		No hysteresis (COMPxHYST[1:0]=00)	-	-	0	-	mV
		Low bystorosis	High speed mode	3		13	
		(COMPxHYST[1:0]=01)	All other power modes	5	8	10	
	Comparator hysteresis	Madium hystorasia	High speed mode	7		26	mV
		(COMPxHYST[1:0]=10)	All other power modes	9	15	19	
		High bystorosis	High speed mode	18		49	
		High hysteresis (COMPxHYST[1:0]=11)	All other power modes	19	31	40	

1. Data based on characterization results, not tested in production.

2. For more details and conditions see Figure 29: Maximum V_{REFINT} scaler startup time from power down.







Symbol	millimeters			inches ⁽¹⁾		
	Min.	Тур.	Max.	Min.	Тур.	Max.
b	0.240	0.290	0.340	0.0094	0.0114	0.0134
D	6.850	7.000	7.150	0.2697	0.2756	0.2815
D1	-	5.500	-	-	0.2165	-
E	6.850	7.000	7.150	0.2697	0.2756	0.2815
E1	-	5.500	-	-	0.2165	-
е	-	0.500	-	-	0.0197	-
Z	-	0.750	-	-	0.0295	-
ddd	-	-	0.080	-	-	0.0031
eee	-	-	0.150	-	-	0.0059
fff	-	-	0.050	-	-	0.0020

1. Values in inches are converted from mm and rounded to 4 decimal digits.





Table 72. UFBGA100 recommended PCB design rules

Dimension	Recommended values
Pitch	0.5
Dpad	0.280 mm
Dsm	0.370 mm typ. (depends on the solder mask registration tolerance)
Stencil opening	0.280 mm
Stencil thickness	Between 0.100 mm and 0.125 mm



Device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.





 Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.



7.2 LQFP100 package information

LQFP100 is a100-pin, 14 x 14 mm low-profile quad flat package.





1. Drawing is not to scale.

Table 73.	LQPF100	package	mechanical	data
		paonago	moonamoa	aata

Symbol	millimeters			inches ⁽¹⁾		
	Min	Тур	Max	Min	Тур	Max
А	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
С	0.090	-	0.200	0.0035	-	0.0079
D	15.800	16.000	16.200	0.6220	0.6299	0.6378
D1	13.800	14.000	14.200	0.5433	0.5512	0.5591
D3	-	12.000	-	-	0.4724	-
E	15.800	16.000	16.200	0.6220	0.6299	0.6378



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Device marking

The following figure gives an example of topside marking orientation versus ball A1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.





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Device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.





 Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.

